

# MC74AC14, MC74ACT14

## Hex Inverter Schmitt Trigger

### High-Performance Silicon-Gate CMOS

The MC74AC14/74ACT14 contains six logic inverters which accept standard CMOS Input signals (TTL levels for MC74ACT14) and provide standard CMOS output levels. They are capable of transforming slowly changing input signals into sharply defined, jitter-free output signals. In addition, they have a greater noise margin than conventional inverters.

The MC74AC14/74ACT14 has hysteresis between the positive-going and negative-going input thresholds (typically 1.0 V) which is determined internally by transistor ratios and is essentially insensitive to temperature and supply voltage variations.

#### Features

- Schmitt Trigger Inputs
- Outputs Source/Sink 24 mA
- MC74ACT14 Has TTL Compatible Inputs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



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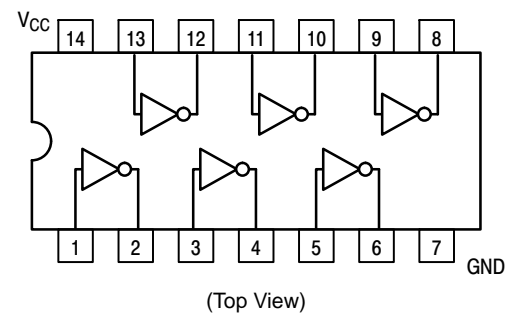
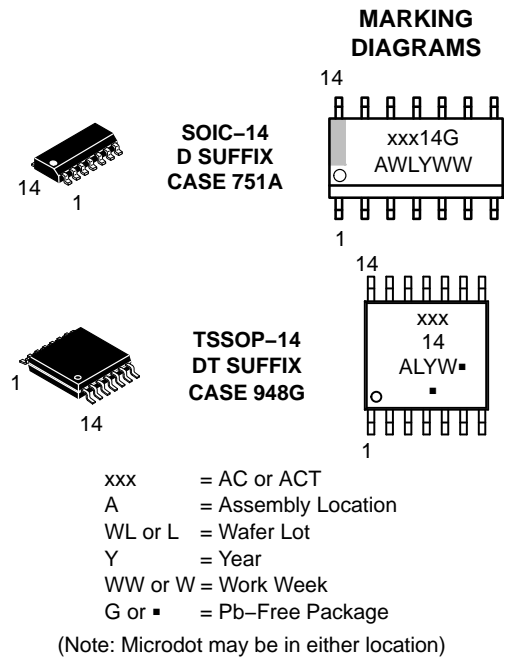


Figure 1. Pinout: 14-Lead Packages Conductors

#### FUNCTION TABLE

Input	Output
A	O
L	H
H	L

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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## MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>I</sub>	DC Input Voltage	-0.5 ≤ V <sub>I</sub> ≤ V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage (Note 1)	-0.5 ≤ V <sub>O</sub> ≤ V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	±20	mA
I <sub>OK</sub>	DC Output Diode Current	±50	mA
I <sub>O</sub>	DC Output Sink/Source Current	±50	mA
I <sub>CC</sub>	DC Supply Current per Output Pin	±50	mA
I <sub>GND</sub>	DC Ground Current per Output Pin	±50	mA
T <sub>STG</sub>	Storage Temperature Range	-65 to +150	°C
T <sub>L</sub>	Lead temperature, 1 mm from Case for 10 Seconds	260	°C
T <sub>J</sub>	Junction temperature under Bias	+150	°C
θ <sub>JA</sub>	Thermal Resistance (Note 2)	SOIC TSSOP 125 170	°C/W
P <sub>D</sub>	Power Dissipation in Still Air at 85°C	SOIC TSSOP 125 170	mW
MSL	Moisture Sensitivity	Level 1	
F <sub>R</sub>	Flammability Rating	Oxygen Index: 30% – 35% UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5) > 2000 > 200 > 1000	V
I <sub>Latch-Up</sub>	Latch-Up Performance	Above V <sub>CC</sub> and Below GND at 85°C (Note 6)	±100 mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. I<sub>O</sub> absolute maximum rating must be observed.
2. The package thermal impedance is calculated in accordance with JESD51-7.
3. Tested to EIA/JESD22-A114-A.
4. Tested to EIA/JESD22-A115-A.
5. Tested to JESD22-C101-A.
6. Tested to EIA/JESD78.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Typ	Max	Unit	
V <sub>CC</sub>	Supply Voltage	'AC	2.0	5.0	6.0	V
		'ACT	4.5	5.0	5.5	
V <sub>in</sub> , V <sub>out</sub>	DC Input Voltage, Output Voltage (Ref. to GND)	0	-	V <sub>CC</sub>	V	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Note 1) 'AC Devices except Schmitt Inputs	V <sub>CC</sub> @ 3.0 V	-	150	-	ns/V
		V <sub>CC</sub> @ 4.5 V	-	40	-	
		V <sub>CC</sub> @ 5.5 V	-	25	-	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time (Note 2) 'ACT Devices except Schmitt Inputs	V <sub>CC</sub> @ 4.5 V	-	10	-	ns/V
		V <sub>CC</sub> @ 5.5 V	-	8.0	-	
T <sub>J</sub>	Junction Temperature (PDIP)	-	-	140	°C	
T <sub>A</sub>	Operating Ambient Temperature Range	-40	25	85	°C	
I <sub>OH</sub>	Output Current – High	-	-	-24	mA	
I <sub>OL</sub>	Output Current – Low	-	-	24	mA	

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

1. V<sub>in</sub> from 30% to 70% V<sub>CC</sub>; see individual Data Sheets for devices that differ from the typical input rise and fall times.
2. V<sub>in</sub> from 0.8 V to 2.0 V; see individual Data Sheets for devices that differ from the typical input rise and fall times.

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## DC CHARACTERISTICS

Symbol	Parameter	V <sub>CC</sub> (V)	74AC		74AC		Unit	Conditions
			T <sub>A</sub> = +25°C		T <sub>A</sub> = -40°C to +85°C			
			Typ	Guaranteed Limits				
V <sub>OH</sub>	Minimum High Level Output Voltage	3.0	2.99	2.9	2.9		V	I <sub>OUT</sub> = -50 μA
		4.5	4.49	4.4	4.4			
		5.5	5.49	5.4	5.4			
		3.0	-	2.56	2.46		V	*V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> -12 mA I <sub>OH</sub> -24 mA -24 mA
		4.5	-	3.86	3.76			
		5.5	-	4.86	4.76			
V <sub>OL</sub>	Maximum Low Level Output Voltage	3.0	0.002	0.1	0.1		V	I <sub>OUT</sub> = 50 μA
		4.5	0.001	0.1	0.1			
		5.5	0.001	0.1	0.1			
		3.0	-	0.36	0.44		V	*V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> 12 mA I <sub>OL</sub> 24 mA 24 mA
		4.5	-	0.36	0.44			
		5.5	-	0.36	0.44			
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	-	±0.1	±1.0		μA	V <sub>I</sub> = V <sub>CC</sub> , GND
I <sub>OLD</sub>	†Minimum Dynamic Output Current	5.5	-	-	75		mA	V <sub>OLD</sub> = 1.65 V Max
I <sub>OHD</sub>		5.5	-	-	-75		mA	V <sub>OHD</sub> = 3.85 V Min
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	-	4.0	40		μA	V <sub>IN</sub> = V <sub>CC</sub> or GND

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

\*All outputs loaded; thresholds on input associated with output under test.

†Maximum test duration 2.0 ms, one output loaded at a time.

NOTE: I<sub>IN</sub> and I<sub>CC</sub> @ 3.0 V are guaranteed to be less than or equal to the respective limit @ 5.5 V V<sub>CC</sub>.

## AC CHARACTERISTICS

Symbol	Parameter	V <sub>CC</sub> * (V)	74AC			74AC		Unit	Figure No.
			T <sub>A</sub> = +25°C C <sub>L</sub> = 50 pF			T <sub>A</sub> = -40°C to +85°C C <sub>L</sub> = 50 pF			
			Min	Typ	Max	Min	Max		
t <sub>PLH</sub>	Propagation Delay	3.3	1.5	9.5	13.5	1.5	15.0	ns	3-5
		5.0	1.5	7.0	10.0	1.5	11.0		
t <sub>PHL</sub>	Propagation Delay	3.3	1.5	7.5	11.5	1.5	13.0	ns	3-5
		5.0	1.5	6.0	8.5	1.5	9.5		

\*Voltage Range 3.3 V is 3.3 V ±0.3 V. Voltage Range 5.0 V is 5.0 V ±0.5 V.

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## INPUT CHARACTERISTICS (unless otherwise specified)

Symbol	Parameter	V <sub>CC</sub> (V)	74AC		74ACT		Test Conditions
			74AC	74ACT	74AC	74ACT	
V <sub>t+</sub>	Maximum Positive Threshold	3.0	2.2	–	–	V	T <sub>A</sub> = Worst Case
		4.5	3.2	2.0	2.0		
		5.5	3.9	2.0	2.0		
V <sub>t–</sub>	Minimum Negative Threshold	3.0	0.5	–	–	V	T <sub>A</sub> = Worst Case
		4.5	0.9	0.8	0.8		
		5.5	1.1	0.8	0.8		
V <sub>h(max)</sub>	Maximum Hysteresis	3.0	1.2	–	–	V	T <sub>A</sub> = Worst Case
		4.5	1.4	1.2	1.2		
		5.5	1.6	1.2	1.2		
V <sub>h(min)</sub>	Minimum Hysteresis	3.0	0.3	–	–	V	T <sub>A</sub> = Worst Case
		4.5	0.4	0.4	0.4		
		5.5	0.5	0.4	0.4		

## DC CHARACTERISTICS

Symbol	Parameter	V <sub>CC</sub> (V)	74ACT		74ACT		Unit	Conditions
			T <sub>A</sub> = +25°C		T <sub>A</sub> = –40°C to +85°C			
			Typ	Guaranteed Limits		Min		
V <sub>OH</sub>	Minimum High Level Output Voltage	4.5	4.49	4.4	4.4	V	I <sub>OUT</sub> = –50 μA	
		5.5	5.49	5.4	5.4			
		4.5	–	3.86	3.76	V	*V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> I <sub>OH</sub> –24 mA	
		5.5	–	4.86	4.76			
V <sub>OL</sub>	Maximum Low Level Output Voltage	4.5	0.001	0.1	0.1	V	I <sub>OUT</sub> = 50 μA	
		5.5	0.001	0.1	0.1			
		4.5	–	0.36	0.44	V	*V <sub>IN</sub> = V <sub>IL</sub> or V <sub>IH</sub> I <sub>OL</sub> 24 mA	
		5.5	–	0.36	0.44			
I <sub>IN</sub>	Maximum Input Leakage Current	5.5	–	±0.1	±1.0	μA	V <sub>I</sub> = V <sub>CC</sub> , GND	
ΔI <sub>CC</sub> T	Additional Max. I <sub>CC</sub> /Input	5.5	0.6	–	1.5	mA	V <sub>I</sub> = V <sub>CC</sub> – 2.1 V	
I <sub>OLD</sub>	†Minimum Dynamic Output Current	5.5	–	–	75	mA	V <sub>OLD</sub> = 1.65 V Max	
I <sub>OHD</sub>		5.5	–	–	–75	mA	V <sub>OHD</sub> = 3.85 V Min	
I <sub>CC</sub>	Maximum Quiescent Supply Current	5.5	–	4.0	40	μA	V <sub>IN</sub> = V <sub>CC</sub> or GND	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

\*All outputs loaded; thresholds on input associated with output under test.

†Maximum test duration 2.0 ms, one output loaded at a time.

## AC CHARACTERISTICS

Symbol	Parameter	V <sub>CC</sub> * (V)	74ACT			74ACT		Unit	Figure No.
			T <sub>A</sub> = +25°C C <sub>L</sub> = 50 pF			T <sub>A</sub> = –40°C to +85°C C <sub>L</sub> = 50 pF			
			Min	Typ	Max	Min	Max		
t <sub>PLH</sub>	Propagation Delay	5.0	1.5	–	11.5	1.0	12.5	ns	3–5
t <sub>PHL</sub>	Propagation Delay	5.0	1.5	–	10.0	1.0	11.0	ns	3–5

\*Voltage Range 5.0 V is 5.0 V ±0.5 V.

## CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C <sub>IN</sub>	Input Capacitance	4.5	pF	V <sub>CC</sub> = 5.0 V
C <sub>PD</sub>	Power Dissipation Capacitance	25	pF	V <sub>CC</sub> = 5.0 V

## MC74AC14, MC74ACT14

### ORDERING INFORMATION

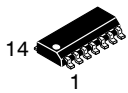
Device	Package	Shipping†
MC74AC14DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74AC14DR2G		2500 / Tape & Reel
NLV74AC14DR2G*		2500 / Tape & Reel
MC74AC14DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel
MC74ACT14DG	SOIC-14 (Pb-Free)	55 Units / Rail
MC74ACT14DR2G		2500 / Tape & Reel
MC74ACT14DTR2G	TSSOP-14 (Pb-Free)	2500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.

# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

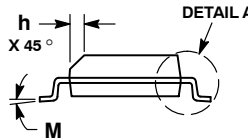
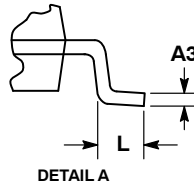
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SCALE 1:1

SOIC-14 NB  
CASE 751A-03  
ISSUE L

DATE 03 FEB 2016

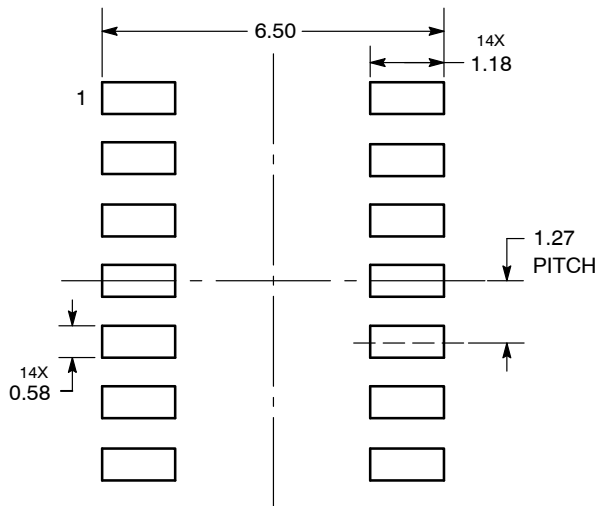


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE PROTRUSION SHALL BE 0.13 TOTAL IN EXCESS OF AT MAXIMUM MATERIAL CONDITION.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSIONS.
5. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	1.35	1.75	0.054	0.068
A1	0.10	0.25	0.004	0.010
A3	0.19	0.25	0.008	0.010
b	0.35	0.49	0.014	0.019
D	8.55	8.75	0.337	0.344
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.019
L	0.40	1.25	0.016	0.049
M	0°	7°	0°	7°

SOLDERING FOOTPRINT\*



DIMENSIONS: MILLIMETERS

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM\*



- XXXXXX = Specific Device Code
- A = Assembly Location
- WL = Wafer Lot
- Y = Year
- WW = Work Week
- G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

STYLES ON PAGE 2

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**SOIC-14**  
**CASE 751A-03**  
**ISSUE L**

DATE 03 FEB 2016

STYLE 1:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. NO CONNECTION  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 2:  
 CANCELLED

STYLE 3:  
 PIN 1. NO CONNECTION  
 2. ANODE  
 3. ANODE  
 4. NO CONNECTION  
 5. ANODE  
 6. NO CONNECTION  
 7. ANODE  
 8. ANODE  
 9. ANODE  
 10. NO CONNECTION  
 11. ANODE  
 12. ANODE  
 13. NO CONNECTION  
 14. COMMON CATHODE

STYLE 4:  
 PIN 1. NO CONNECTION  
 2. CATHODE  
 3. CATHODE  
 4. NO CONNECTION  
 5. CATHODE  
 6. NO CONNECTION  
 7. CATHODE  
 8. CATHODE  
 9. CATHODE  
 10. NO CONNECTION  
 11. CATHODE  
 12. CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 5:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. NO CONNECTION  
 7. COMMON ANODE  
 8. COMMON CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. ANODE/CATHODE  
 12. ANODE/CATHODE  
 13. NO CONNECTION  
 14. COMMON ANODE

STYLE 6:  
 PIN 1. CATHODE  
 2. CATHODE  
 3. CATHODE  
 4. CATHODE  
 5. CATHODE  
 6. CATHODE  
 7. CATHODE  
 8. ANODE  
 9. ANODE  
 10. ANODE  
 11. ANODE  
 12. ANODE  
 13. ANODE  
 14. ANODE

STYLE 7:  
 PIN 1. ANODE/CATHODE  
 2. COMMON ANODE  
 3. COMMON CATHODE  
 4. ANODE/CATHODE  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. ANODE/CATHODE  
 8. ANODE/CATHODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. COMMON CATHODE  
 12. COMMON ANODE  
 13. ANODE/CATHODE  
 14. ANODE/CATHODE

STYLE 8:  
 PIN 1. COMMON CATHODE  
 2. ANODE/CATHODE  
 3. ANODE/CATHODE  
 4. NO CONNECTION  
 5. ANODE/CATHODE  
 6. ANODE/CATHODE  
 7. COMMON ANODE  
 8. COMMON ANODE  
 9. ANODE/CATHODE  
 10. ANODE/CATHODE  
 11. NO CONNECTION  
 12. ANODE/CATHODE  
 13. ANODE/CATHODE  
 14. COMMON CATHODE

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# MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS

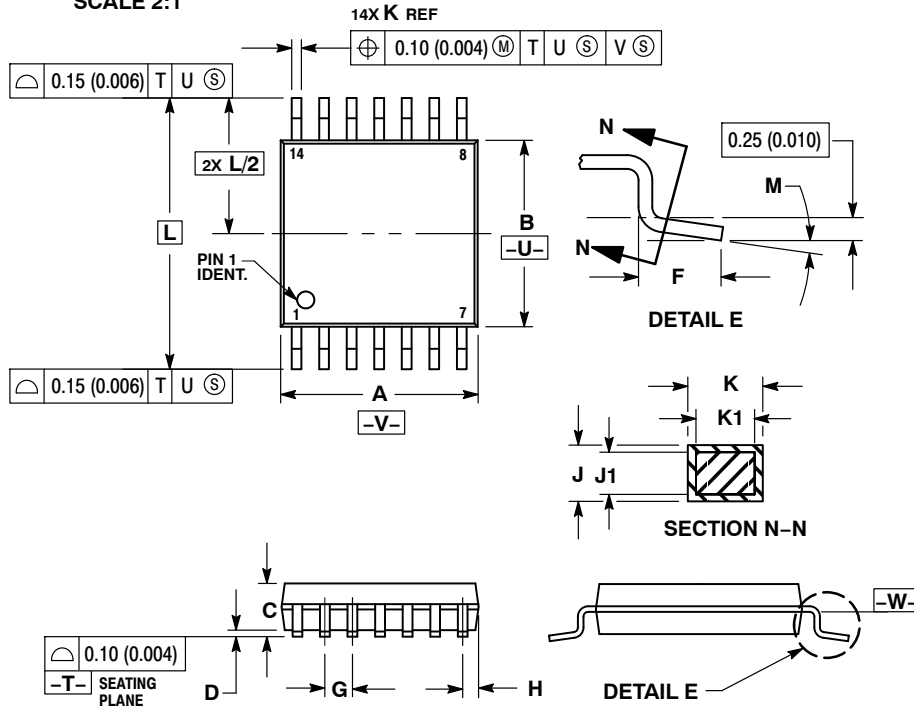
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**TSSOP-14 WB**  
CASE 948G  
ISSUE C

DATE 17 FEB 2016

SCALE 2:1

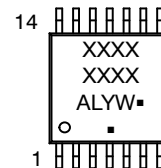


**NOTES:**

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
- DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
- DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
- TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
- DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

**GENERIC MARKING DIAGRAM\***

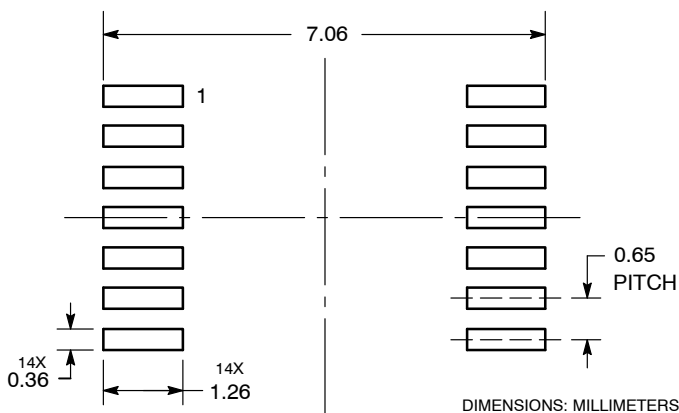


- A = Assembly Location
- L = Wafer Lot
- Y = Year
- W = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

**SOLDERING FOOTPRINT**



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